# TLV4H290-SEP および TLV4H390-SEP 宇宙向け強化プラスチックの耐放射線高精度クワッド コンパレータ

1 特長

- VID
  - V62/24636-01XE
  - V62/24636-02XE
- 放射線 - トータル ドーズ効果 (TID)
  - 30krad (Si) まで吸収線量 (TID) 特性を評価済み
  - 30krad (Si) まで ELDRS フリー
  - 30krad (Si) まで RHA/RLAT
- 放射線 - シングル イベント効果（SEE）
  - SEL 耐性：LET = 43MeV·cm2 /mg
  - SET 特性：LET = 43MeV·cm2 /mg
- 宇宙向け強化プラスチック
  - 管理されたベースライン
  - 単一のアセンブリ / テスト施設
  - 単一の製造施設
  - 長期にわたる製品ライフ サイクル
  - 製品のトレーサビリティ
- 電源電圧範囲：1.65V〜5.5V
- 高精度入力オフセット電圧：300μV
- フォルト トレラントな入力
- 伝搬遅延時間：100ns (代表値)
- 低い静止電流：チャネルあたり 25μA
- 低い入力バイアス電流：5pA
- オープン ドレイン出力オプション (TLV4H290-SEP)
- プッシュプル出力オプション (TLV4H390-SEP)
- 全温度範囲 (-55℃〜125℃)
- ESD 保護：2kV

2 アプリケーション

- 低軌道衛星用途のサポート
- 電化製品
- ビル オートメーション
- ファクトリ オートメーション / 制御
- モーター ドライブ
- インフォテインメントおよびクラスタ
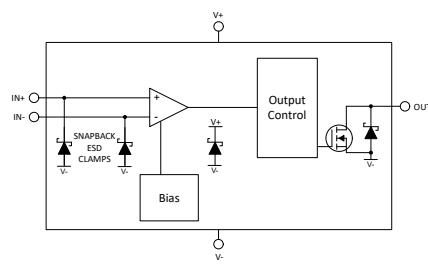
3 概要

TLV4H290-SEP および TLV4H390-SEP は、入力オフセット電圧が低く、速度と消費電力の組み合わせが非常に優れており、伝搬遅延が 100ns のクワッド チャネル コンパレータです。動作電圧範囲は 1.65V〜5.5V で、静止時消費電流は 1 チャネルあたり 25μA です。

このデバイス ファミリにはフォルト トレラントな入力が内蔵されており、コンパレータに電源が印加されていない場合でも入力ピンに電圧を印加できるため、電源シーケンシングが課題となるアプリケーションに最適です。同様に、これらのコンパレータは最高 6V までのフォルト トレラントな入力で損傷を受けず、出力の位相反転も起きません。

TLV4H290-SEP コンパレータにはオープン ドレイン出力段があり、電源電圧の下や上にプルできるため、レベル変換に適しています。TLV4H390-SEP にはプッシュプル出力段があり、シンク電流とソース電流の両方を供給できます。

TLV4H290-SEP および TLV4H390-SEP は、プラスチックの 14 ピン SOT-23 パッケージで供給され、放射線耐性は最大 43MeV·cm^2 /mg です。

製品情報

部品番号	パッケージ [1]	本体サイズ (公称) [2]
TLV4H290-SEP、TLV4H390-SEP	SOT-23 (14)	4.2 mm × 2.0mm

(1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値で、該当する場合はピンも含まれます。
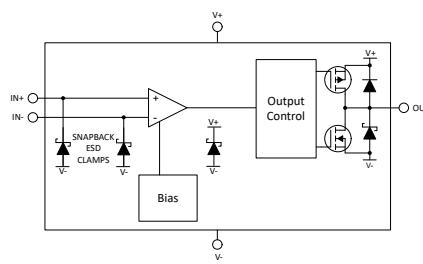
オープン ドレイン出力のブロック図

プッシュプル出力のブロック図

English Data Sheet: SNOSDF0

Table of Contents

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

4 Pin Configuration and Functions

4.1 Pin Functions:TLV4H290-SEP and TLV4H390-SEP Quad
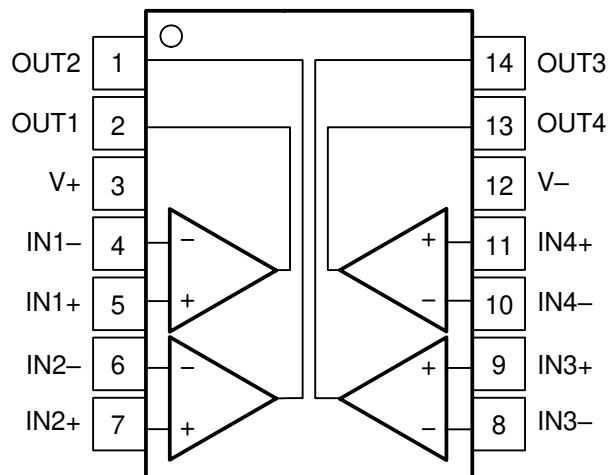
図 4-1. DYY Package
14-Pin SOT-23
Top View

表 4-1. Pin Functions: TLV4H290-SEP and TLV4H390-SEP Quad

PIN		I/O	DESCRIPTION
NAME	NO.		
OUT2	1	O	Output pin of the comparator 2
OUT1	2	O	Output pin of the comparator1
V+	3	—	Positive supply
IN1–	4	I	Negative input pin of the comparator 1
IN1+	5	I	Positive input pin of the comparator 1
IN2–	6	I	Negative input pin of the comparator 2
IN2+	7	I	Positive input pin of the comparator 2
IN3–	8	I	Negative input pin of the comparator 3
IN3+	9	I	Positive input pin of the comparator 3
IN4–	10	I	Negative input pin of the comparator 4
IN4+	11	I	Positive input pin of the comparator 4
V–	12	—	Negative supply
OUT4	13	O	Output pin of the comparator 4
OUT3	14	O	Output pin of the comparator 3

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)[1]

	MIN	MAX	UNIT
Supply voltage: V_S = (V+) – (V–)	–0.3	6	V
Input pins (IN+, IN–) from (V–)[2]	–0.3	6	V
Current into Input pins (IN+, IN–)	–10	10	mA
Output (OUT) from (V–), open-drain only[3]	–0.3	6	V
Output (OUT) from (V–), push-pull only	–0.3	(V+) + 0.3	V
Output short circuit duration[4]		10	s
Junction temperature, T_J		150	°C
Storage temperature, T_{stg}	–65	150	°C

(1) Operation outside the Absolute Maximum Ratings can cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this can affect device reliability, functionality, performance, and shorten the device lifetime.
(2) Input terminals are diode-clamped to (V–). Input signals that can swing more than 0.3V beyond the supply rails must be current-limited to 10mA or less. Additionally, Inputs (IN+, IN–) can be greater than (V+) and OUT as long as input is within the –0.3V to 6V range
(3) Output (OUT) for open drain can be greater than (V+) and inputs (IN+, IN–) as long as the input is within the –0.3V to 6V range
(4) Short-circuit to (V–) or (V+).

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	±1000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Supply voltage: V_S = (V+) – (V–)	1.65	5.5	V
Input voltage range (IN+, IN–) from (V–)	–0.3	5.7	V
Ambient temperature, T_A	–55	125	°C

5.4 Thermal Information

THERMAL METRIC[1]		TLV4H290-SEP, TLV4H390-SEP	UNIT
		DYY (SOT23)	
		14 PINS	
R_{qJA}	Junction-to-ambient thermal resistance	218.1	°C/W
$R_{qJC(top)}$	Junction-to-case (top) thermal resistance	127.0	°C/W
R_{qJB}	Junction-to-board thermal resistance	129.6	°C/W
y_{JT}	Junction-to-top characterization parameter	24.7	°C/W
y_{JB}	Junction-to-board characterization parameter	126.8	°C/W
$R_{qJC(bot)}$	Junction-to-case (bottom) thermal resistance	–	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics appnote.

5.5 Electrical Characteristics

For V_S (Total Supply Voltage) = (V+) – (V–) = 5V, V_{CM} = (V–) at T_A = 25°C (Unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V_{OS}	Input offset voltage	V_S = 1.8V and 5V	–3	±0.3	3	mV
V_{OS}	Input offset voltage	V_S = 1.8V and 5V, T_A = –55°C to +125°C	–4		4	
dV_{IO}/dT	Input offset voltage drift	V_S = 1.8V and 5V, T_A = –55°C to +125°C		±0.5		µV/°C
POWER SUPPLY						
I_Q	Quiescent current per comparator	V_S = 1.8V and 5V, No Load, Output Low		25	35	µA
I_Q	Quiescent current per comparator	V_S = 1.8V and 5V, No Load, Output Low, T_A = –55°C to +125°C			40	
PSRR	Power-supply rejection ratio	V_S = 1.8V to 5V, T_A = –55°C to +125°C		95		dB
INPUT BIAS CURRENT						
I_B	Input bias current	V_{CM} = V_S/2		5		pA
I_{OS}	Input offset current	V_{CM} = V_S/2		1		pA
INPUT CAPACITANCE						
C_{ID}	Input Capacitance, Differential	V_{CM} = V_S/2		2		pF
C_{IC}	Input Capacitance, Common Mode	V_{CM} = V_S/2		3		pF
INPUT VOLTAGE RANGE						
$V_{CM-Range}$	Common-mode voltage range	V_S = 1.8V and 5V, T_A = –55°C to +125°C	(V–) – 0.2		(V+) - 1.5	V
CMRR	Common-mode rejection ratio	V_S = 5V, (V–) < V_{CM} < (V+ - 1.5), T_A = –55°C to +125°C		70		dB
OPEN-LOOP GAIN						
A_{VD}	Large signal differential voltage amplification	For open-drain version only		200		V/mV
OUTPUT						
V_{OL}	Voltage swing from (V–)	I_{SINK} = 4mA, T_A = 25°C		75	125	mV
V_{OL}	Voltage swing from (V–)	I_{SINK} = 4mA, T_A = –55°C to +125°C			175	mV
V_{OH}	Voltage swing from (V+)	I_{SOURCE} = 4mA, T_A = 25°C (push-pull only)		75	125	mV
V_{OH}	Voltage swing from (V+)	I_{SOURCE} = 4mA, T_A = –55°C to +125°C (push-pull only)			175	mV
I_{LKG}	Open-drain output leakage current	V_{PULLUP} = (V+), T_A = 25°C (open drain only)		10		nA
I_{SC}	Short-circuit current	V_S = 5V, Sinking	90	100		mA
I_{SC}	Short-circuit current	V_S = 5V, Sourcing (push-pull only)	90	100		mA

資料に関するフィードバック (ご意見やお問い合わせ) を送信

English Data Sheet: SNOSDF0

5.6 Switching Characteristics

For V_S (Total Supply Voltage) = (V+) – (V–) = 5V, V_{CM} = V_S / 2, C_L = 15pF at T_A = 25°C (Unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT						
T_{PD-HL}	Propagation delay time, high-to-low	V_{ID} = –100mV; Delay from mid-point of input to mid-point of output (R_P = 2.5KΩ for open drain only)		100		ns
T_{PD-LH}	Propagation delay time, low-to-high	V_{ID} = 100mV; Delay from mid-point of input to mid-point of output (for push-pull only)		115		ns
T_{PD-LH}	Propagation delay time, low-to-high	V_{ID} = 100mV; Delay from mid-point of input to mid-point of output (R_P = 2.5KΩ for open drain only)		150		ns
T_{FALL}	5V Output Fall Time, 80% to 20%	V_{ID} = –100mV		3		ns
T_{RISE}	5V Output Rise Time, 20% to 80%	V_{ID} = 100mV, for push-pull only		3		ns
F_{TOGGLE}	5V, Toggle Frequency	V_{ID} = 100mV (R_P = 2.5KΩ for open drain only)		3		MHz
POWER ON TIME						
P_{ON}	Power on-time	V_S = 1.8V and 5V, V_{CM} = (V–), V_{ID} = –0.1V, $V_{PULL-UP}$ = V_S / 2, Delay from V_S / 2 to V_{OUT} = 0.1 x V_S / 2 (R_P = 2.5KΩ for open drain only)		30		µs

6 Typical Characteristics

T_A = 25°C, V_S = 5V, R_{PULLUP} = 2.5k, C_L = 15pF, V_{CM} = 0V, $V_{UNDERDRIVE}$ = 100mV, $V_{OVERDRIVE}$ = 100mV unless otherwise noted.
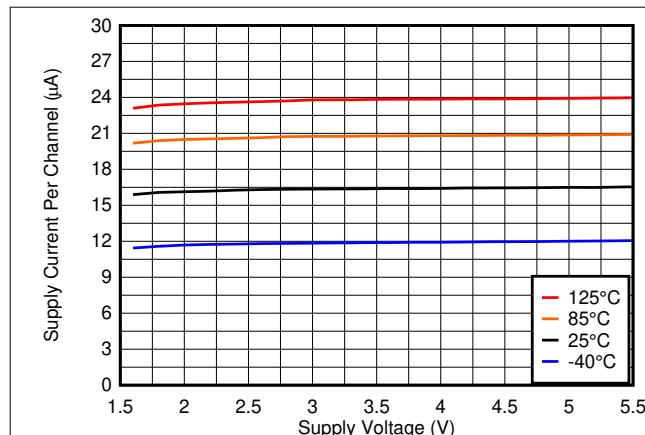

図 6-1. Supply Current vs. Supply Voltage
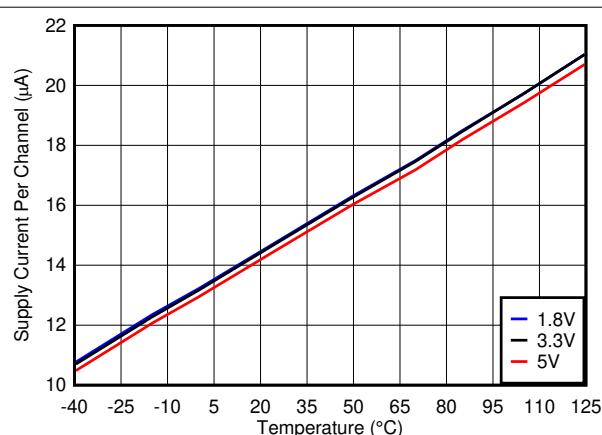
図 6-2. Supply Current vs. Temperature
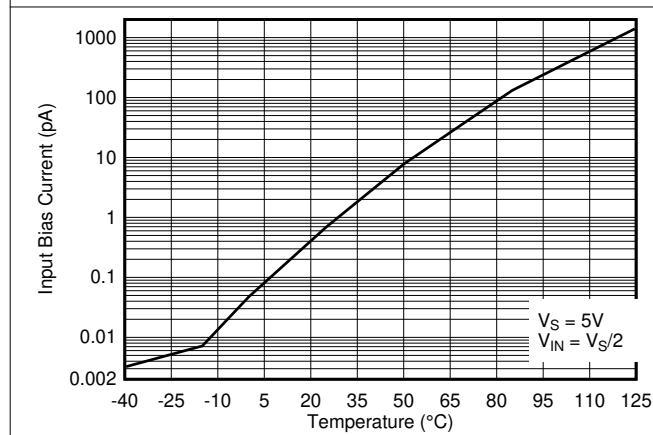
図 6-3. Input Bias Current vs. Temperature
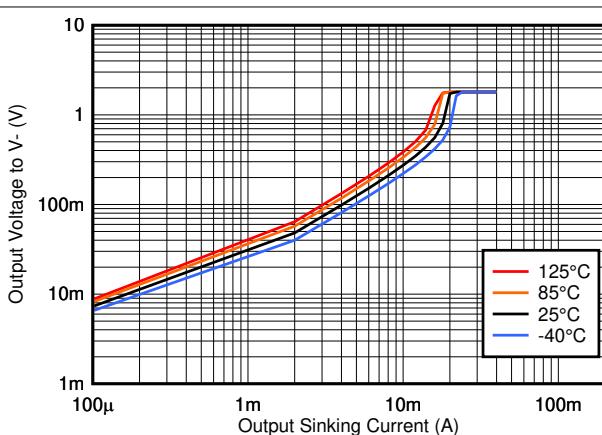

図 6-4. Output Sinking Current vs. Output Voltage, 1.8V
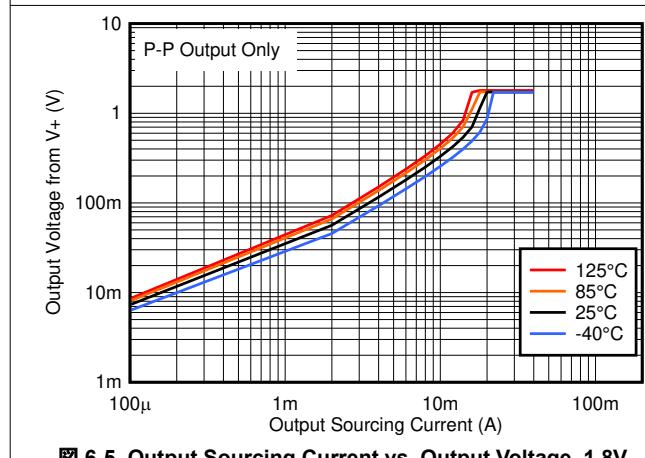

図 6-5. Output Sourcing Current vs. Output Voltage, 1.8V
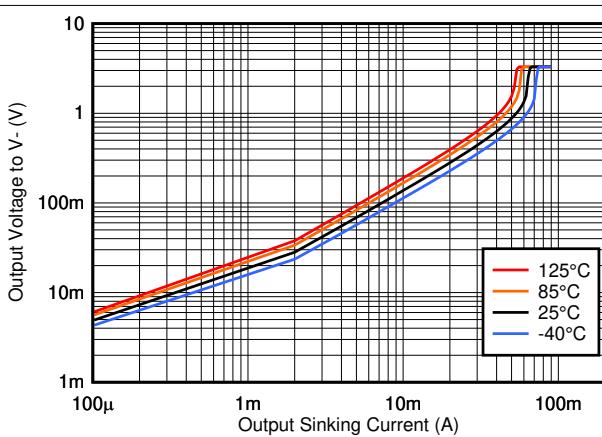
図 6-6. Output Sinking Current vs. Output Voltage, 3.3V

6 Typical Characteristics (continued)

T_A = 25°C, V_S = 5V, R_{PULLUP} = 2.5k, C_L = 15pF, V_{CM} = 0V, $V_{UNDERDRIVE}$ = 100mV, $V_{OVERDRIVE}$ = 100mV unless otherwise noted.
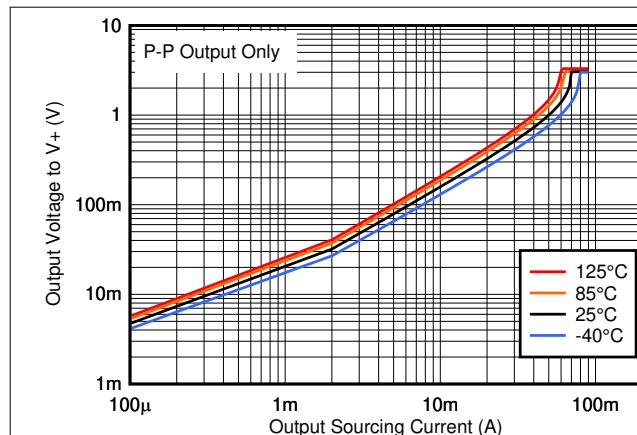
**図 6-7. Output Sourcing Current vs. Output Voltage, 3.3V**
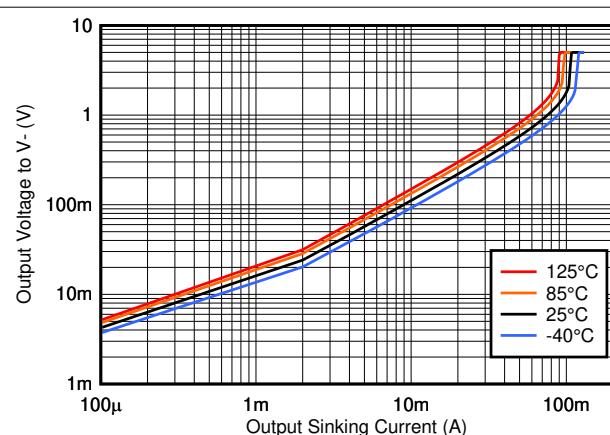
図 6-8. Output Sinking Current vs. Output Voltage, 5V
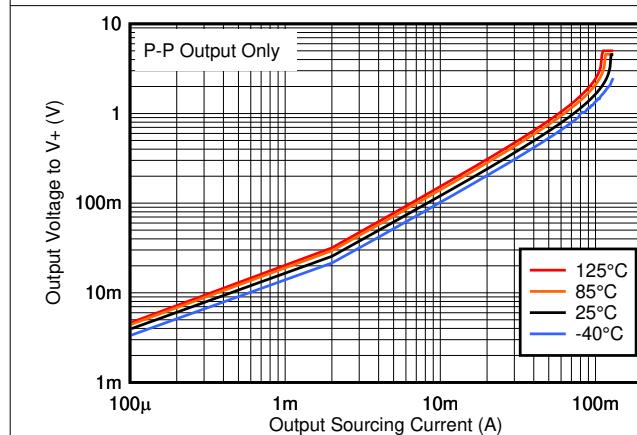
**図 6-9. Output Sourcing Current vs. Output Voltage, 5V**
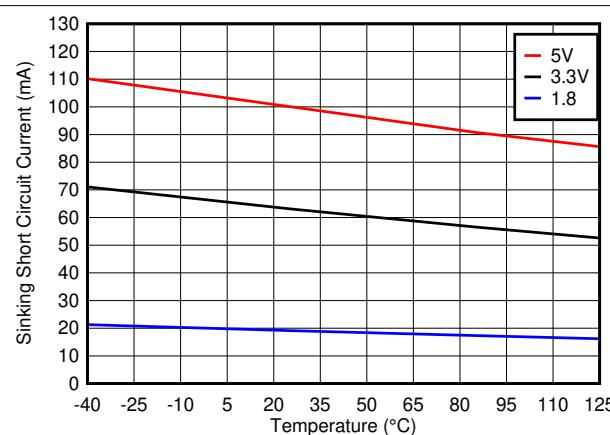
図 6-10. Sinking Short Circuit Current vs. Temperature
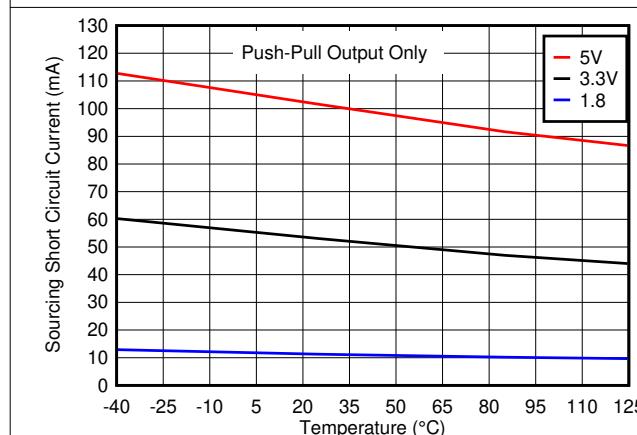
図 6-11. Sourcing Short Circuit Current vs. Temperature
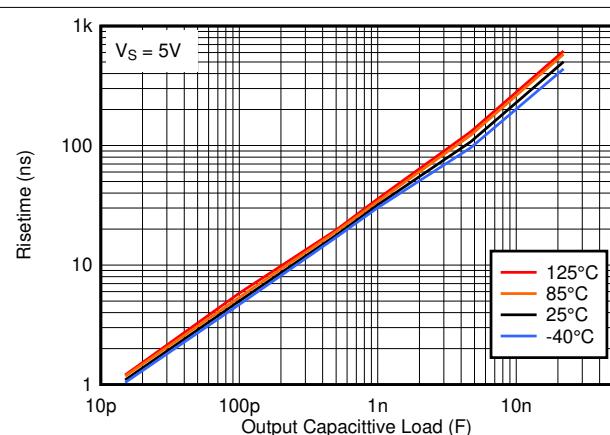
図 6-12. Risetime vs. Capacitive Load

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

6 Typical Characteristics (continued)

T_A = 25°C, V_S = 5V, R_{PULLUP} = 2.5k, C_L = 15pF, V_{CM} = 0V, $V_{UNDERDRIVE}$ = 100mV, $V_{OVERDRIVE}$ = 100mV unless otherwise noted.
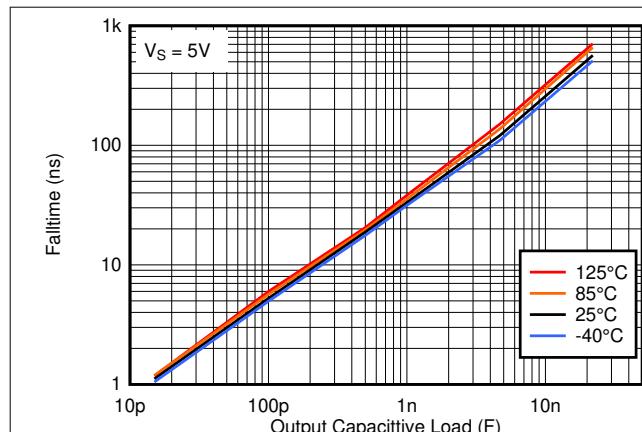

図 6-13. Falltime vs. Capacitive Load
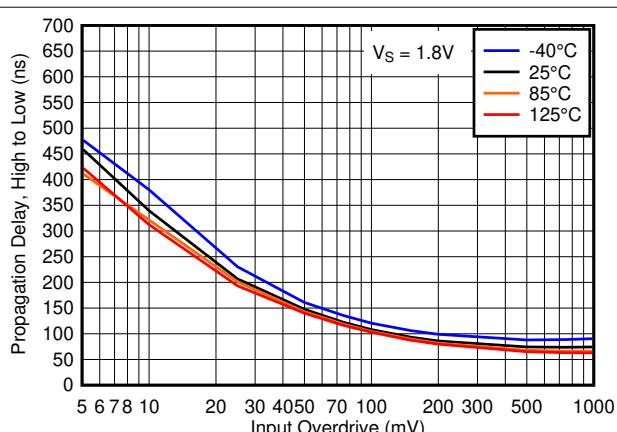
図 6-14. Propagation Delay, High to Low, 1.8V
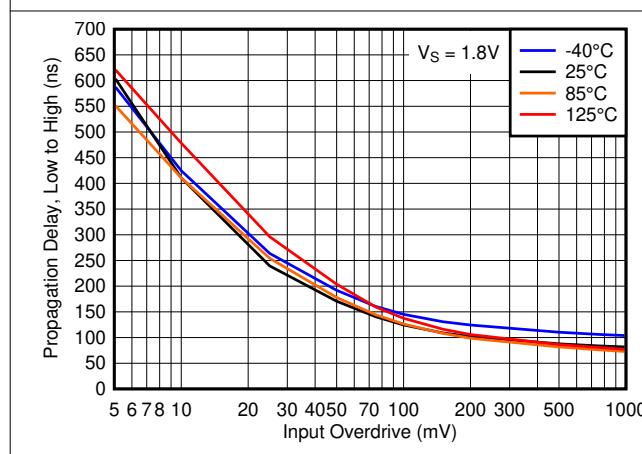
図 6-15. Propagation Delay, Low to High, 1.8V
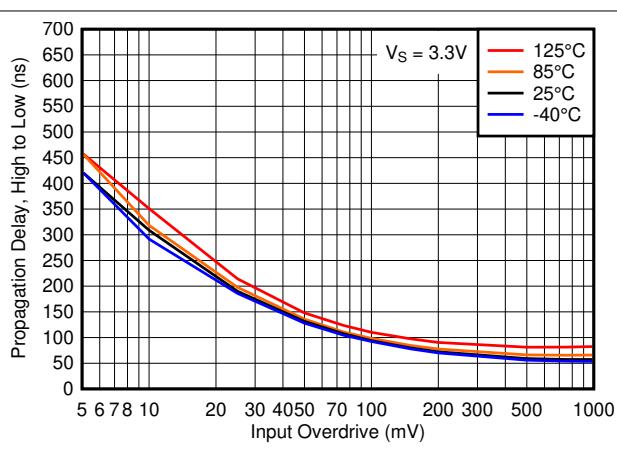

図 6-16. Propagation Delay, High to Low, 3.3V
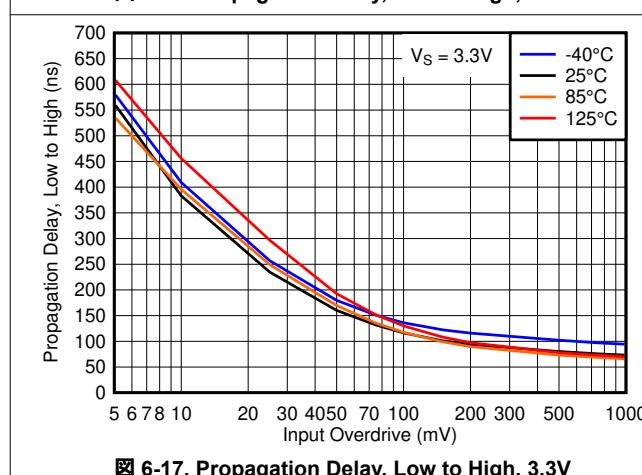
図 6-17. Propagation Delay, Low to High, 3.3V
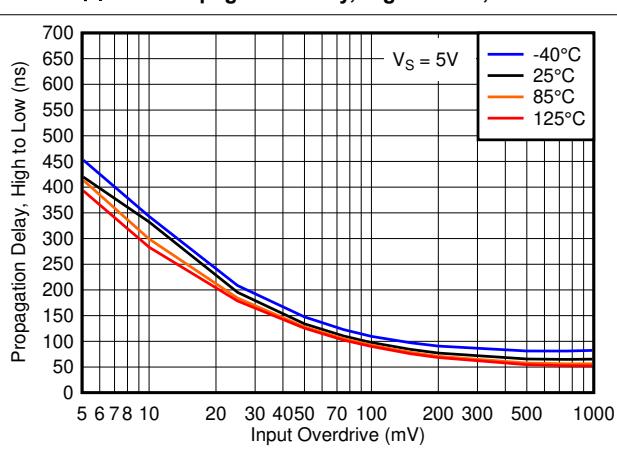
図 6-18. Propagation Delay, High to Low, 5V

6 Typical Characteristics (continued)

T_A = 25°C, V_S = 5V, R_{PULLUP} = 2.5k, C_L = 15pF, V_{CM} = 0V, $V_{UNDERDRIVE}$ = 100mV, $V_{OVERDRIVE}$ = 100mV unless otherwise noted.
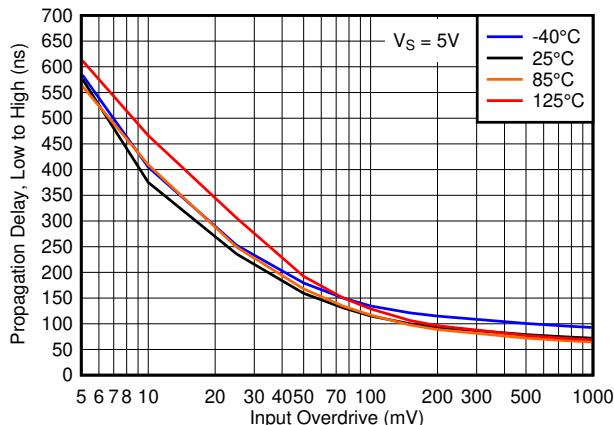
図 6-19. Propagation Delay, Low to High, 5V
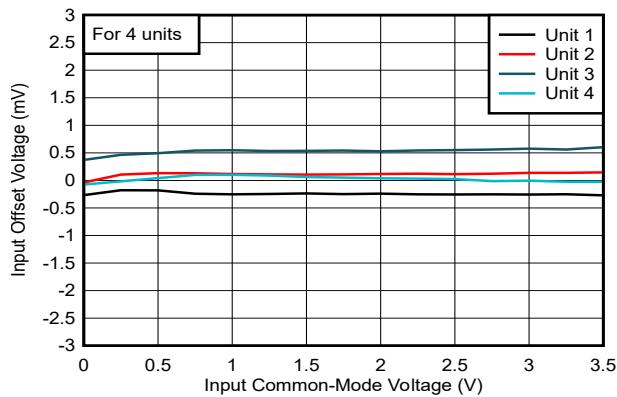
図 6-20. Offset Voltage vs. Common-Mode at 125°C, 5V
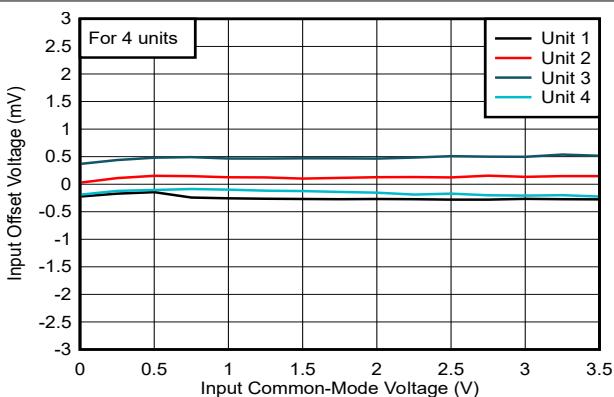
図 6-21. Offset Voltage vs. Common-Mode at 25°C, 5V
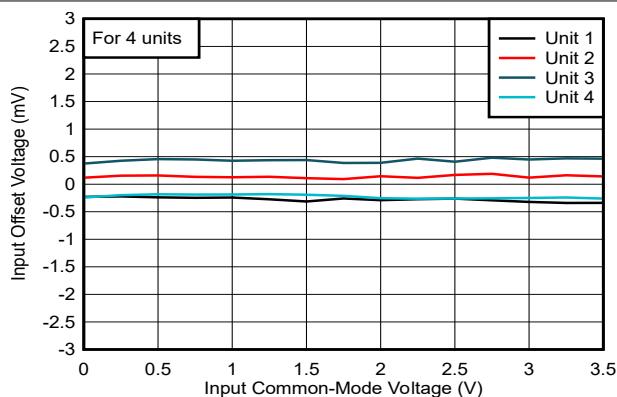
図 6-22. Offset Voltage vs. Common-Mode at -40°C, 5V
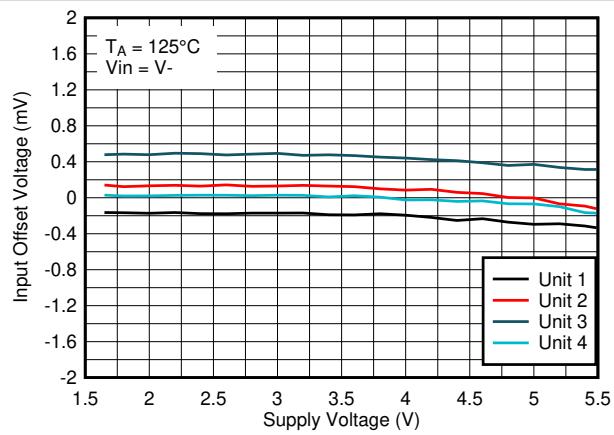
図 6-23. Offset Voltage vs. Supply Voltage at 125°C, V_{IN}=V-

図 6-24. Offset Voltage vs. Supply Voltage at 25°C, V_{IN}=V-
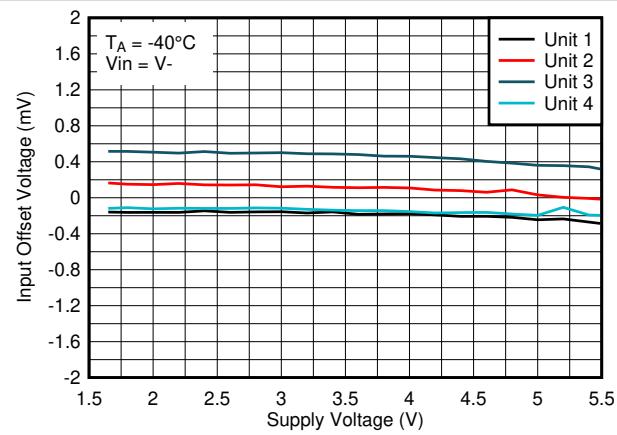
Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

6 Typical Characteristics (continued)

T_A = 25°C, V_S = 5V, R_{PULLUP} = 2.5k, C_L = 15pF, V_{CM} = 0V, $V_{UNDERDRIVE}$ = 100mV, $V_{OVERDRIVE}$ = 100mV unless otherwise noted.
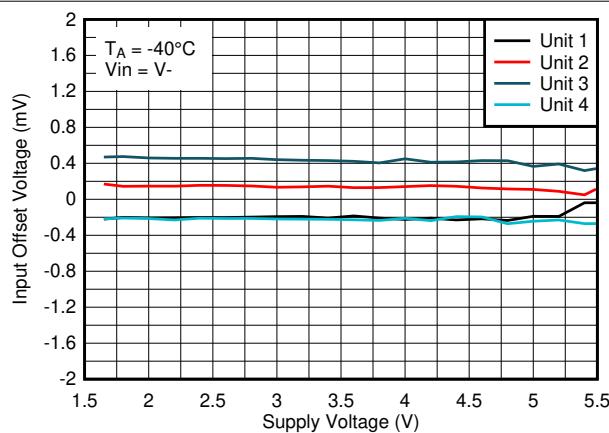
図 6-25. Offset Voltage vs. Supply Voltage at -40°C, V_{IN}=V-

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

7 Detailed Description

7.1 Overview

The TLV4H290-SEP and TLV4H390-SEP devices are quad channel Space Grade Enhanced Products, micro-power comparators with push-pull and open-drain outputs and low input offset voltage. Operating down to 1.65V while only consuming only 25µA per channel. The radiation hardened TLVLV4H290-SEP and TLV4390-SEP are designed for low orbit and space applications. Fault-tolerant inputs can tolerate input transients up to the absolute maximum voltage without damage or false outputs.

7.2 Functional Block Diagram
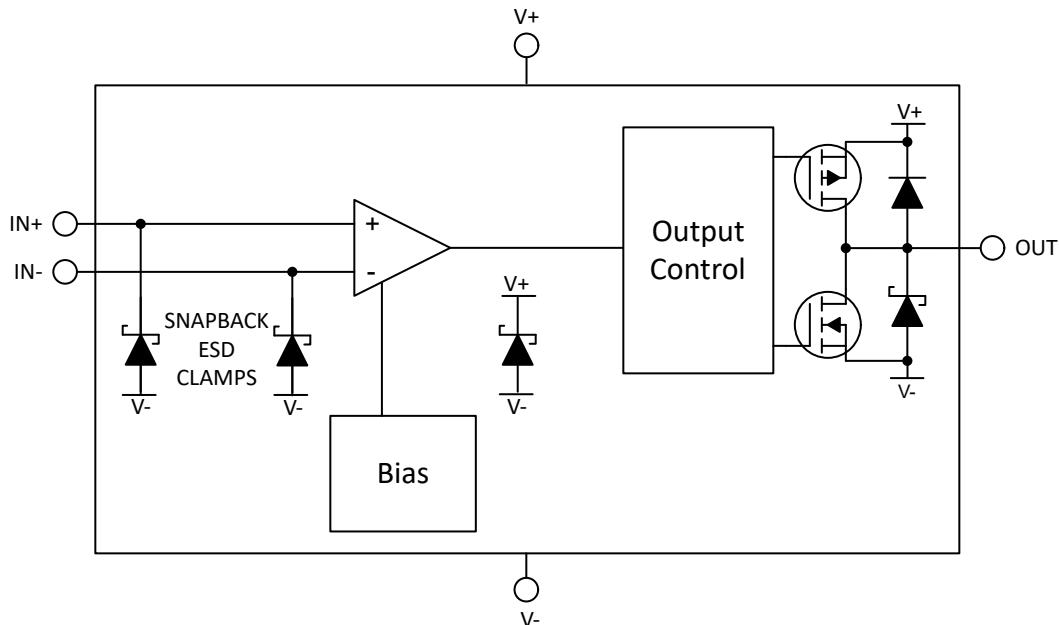
7.3 Feature Description

The TLV4H290-SEP (open-drain output) and TLV4H390-SEP (push-pull output) devices are micro-power comparators that have low input offset voltages and are capable of operating at low voltages. The TLV4H290-SEP and TLV4H390-SEP family feature push-pull and open-drain output stage options and fault-tolerant input pins.

7.4 Device Functional Modes

7.4.1 Outputs

7.4.1.1 TLV4H290-SEP Open Drain Output

The TLV4H290-SEP features an open-drain (also commonly called open collector) sinking-only output stage enabling the output logic levels to be pulled up to an external voltage from 0V up to 5.5V, independent of the comparator supply voltage (V_S). The open-drain output also allows logical OR'ing of multiple open drain outputs and logic level translation. TI recommends setting the pull-up resistor current to between 100uA and 1mA. Lower pull-up resistor values help increase the rising edge risetime, but at the expense of increasing V_{OL} and higher power dissipation. The risetime is dependent on the time constant of the total pull-up resistance and total load capacitance. Large value pull-up resistors (>1MΩ) create an exponential rising edge due to the RC time constant and increase the risetime.

Unused open drain outputs must be left floating, or can be tied to the V- pin if floating pins are not allowed. While an individual output can typically sink up to 125mA, the total combined current for all channels must be less than 200mA.

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

7.4.1.2 TLV4H390-SEP Push-Pull Output

The TLV4H390-SEP features a push-pull output stage capable of both sinking and sourcing current. This allows driving loads such as LED's and MOSFET gates, as well as eliminating the need for a power-wasting external pull-up resistor. The push-pull output must never be connected to another output.

Unused push-pull outputs must be left floating, and never tied to a supply, ground, or another output. While an individual output can typically sink and source up to 100mA, the total combined current for all channels must be less than 200mA.

7.4.2 Inputs

7.4.2.1 Fault Tolerant Inputs

The TLV4H290-SEP and TLV4H390-SEP inputs are fault tolerant up to 5.5V independent of V_S. Fault tolerant is defined as maintaining the same high input impedance when V_S is unpowered or within the recommended operating ranges.

The fault tolerant inputs can be any value between 0V and 5.5V, even while V_S is zero or ramping up or down. This feature avoids power sequencing issues as long as the input voltage range and supply voltage are within the specified ranges. This is possible since the inputs are not clamped to V+ and the input current maintains the high impedance value even when a higher voltage is applied to the inputs.

As long as one of the input pins remains within the valid input common-mode range, and the supply voltage is valid, the output state is correct.

The following is a summary of input voltage excursions and the outcomes:
1. When both IN- and IN+ are within the specified input common-mode voltage range:
    a. If IN- is higher than IN+ and the offset voltage, the output is low.
    b. If IN- is lower than IN+ and the offset voltage, the output is high.
2. When IN- is outside the specified input common-mode voltage range and IN+ is within the specified common-mode voltage range, the output is low.
3. When IN+ is higher than the specified input common-mode voltage range and IN- is within the specified input common-mode voltage range, the output is high
4. When IN- and IN+ are both outside the specified input common-mode voltage range, the output is **indeterminate** (random). *Do not* operate in this region.

Operating outside the specified input range can cause changes in specifications such as propagation delay and input bias current, which can lead to unpredictable behavior.

7.4.2.2 Input Protection

The input bias current is typically 5pA for input voltages between V+ and V-. The comparator inputs are protected from reverse voltage by the internal ESD diodes connected to V-. As the input voltage goes under V-, or above the input Absolute Maximum ratings the protection diodes become forward biased and begin to conduct causing the input bias current to increase exponentially. Input bias current typically doubles for each 10°C temperature increase.

If the inputs are to be connected to a low impedance source, such as a power supply or buffered reference line, TI recommends adding a current-limiting resistor in series with the input to limit any transient currents if the clamps conduct. The current must be limited 10mA or less. This series resistance can be part of any resistive input dividers or networks.

7.4.3 ESD Protection

The TLV4H290-SEP and TLV4H390-SEP family incorporates internal ESD protection circuits on all pins. The inputs, and the open-drain output, use a proprietary "snapback" type ESD clamp from each pin to V-, which allows the pins to exceed the supply voltage (V+). While shown as Zener diodes, snapback "short" and go low impedance (like an SCR) when the threshold is exceeded, as opposed to clamping to a defined voltage like a Zener.

The TLV4H290-SEP open-drain output protection also consists of a ESD clamp between the output and V- to allow the output to be pulled above V+ to a maximum of 5.5V.

The TLV4H390-SEP push-pull output protection consists of a ESD clamp between the output and V-, but also includes a ESD diode clamp to V+, as the output must not exceed the supply rails.

If the inputs are to be connected to a low impedance source, such as a power supply or buffered reference line, TI recommends adding a current-limiting resistor in series with the input to limit any transient currents the clamps conduct. The current must be limited 10mA or less. This series resistance can be part of any resistive input dividers or networks. TI does not specify the performance of the ESD clamps and external clamping must be added if the inputs or output exceeds the maximum ratings as part of normal operation.

7.4.4 Unused Inputs

If a channel is not to be used, DO NOT tie the inputs together. Due to the high equivalent bandwidth and low offset voltage, tying the inputs directly together can cause high frequency "chatter" as the device triggers on it's own internal wideband noise. Instead, the inputs must be tied to any available voltage that resides within the specified input voltage range and provides a minimum of 50mV differential voltage. For example, one input can be grounded and the other input connected to a reference voltage, or even V+ as long as the input is directly connected to the V+ pin (to avoid transients).

7.4.5 Hysteresis

The TLV4H290-SEP and TLV4H390-SEP family does not have internal hysteresis. Due to the wide effective bandwidth and low input offset voltage, there is a possiblity for the output to "chatter" when the absolute differential voltage near zero as the comparator triggers on it's own internal wideband noise. This is normal comparator behavior and is expected. TI recommends that the user add external hysteresis if slow moving signals are expected. See セクション 8.1.2 in the following section.

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0

8 Application and Implementation

> 注
>
> Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Basic Comparator Definitions

8.1.1.1 Operation

The basic comparator compares the input voltage (V_{IN}) on one input to a reference voltage (V_{REF}) on the other input. In the 図 8-1 example below, if V_{IN} is less than V_{REF}, the output voltage (V_O) is logic low (V_{OL}). If V_{IN} is greater than V_{REF}, the output voltage (V_O) is at logic high (V_{OH}). 表 8-1 summarizes the output conditions. The output logic can be inverted by simply swapping the input pins.

表 8-1. Output Conditions

Inputs Condition	Output
IN+ > IN-	HIGH (V_{OH})
IN+ = IN-	Indeterminate (chatters - see Hysteresis)
IN+ < IN-	LOW (V_{OL})

8.1.1.2 Propagation Delay

There is a delay between from when the input crosses the reference voltage and the output responds. This is called the Propagation Delay. Propagation delay can be different between high-to low and low-to-high input transitions. This is shown as t_{pLH} and t_{pHL} in 図 8-1 and is measured from the mid-point of the input to the midpoint of the output.
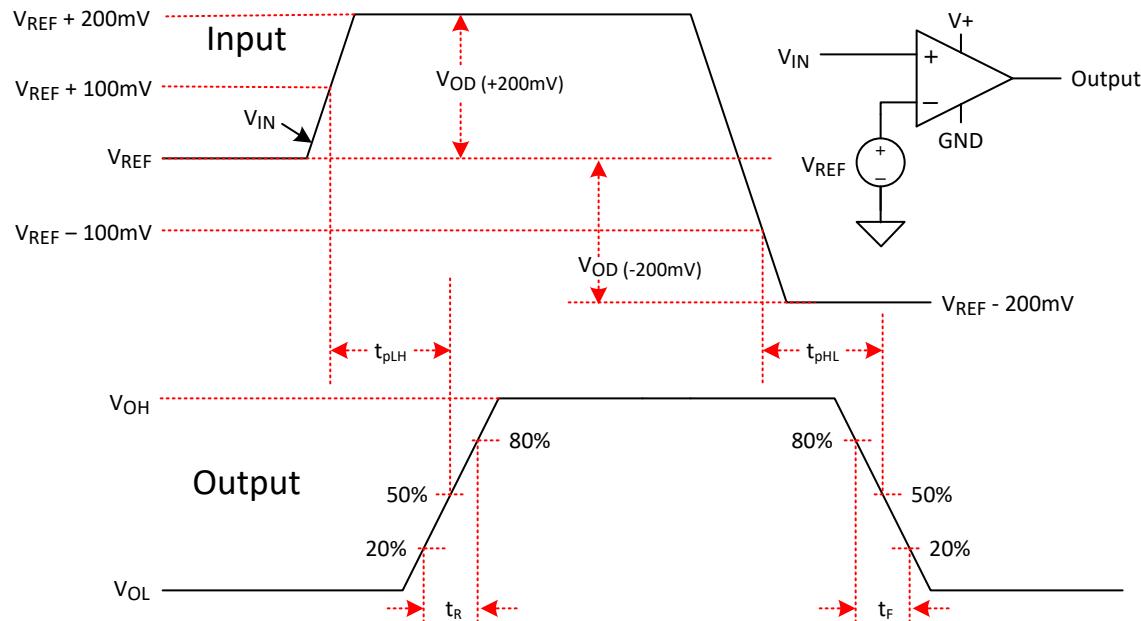
図 8-1. Comparator Timing Diagram

8.1.1.3 Overdrive Voltage

The overdrive voltage, V_{OD}, is the amount of input voltage beyond the reference voltage (and not the total input peak-to-peak voltage). The overdrive voltage is 100mV as shown in the 図 8-1 example. The overdrive voltage can influence the propagation delay (t_p). The smaller the overdrive voltage, the longer the propagation delay, particularly when <100mV. If the fastest speeds are desired, TI recommends applying the highest amount of overdrive possible.

The risetime (t_r) and falltime (t_f) is the time from the 20% and 80% points of the output waveform.

8.1.2 Hysteresis

The basic comparator configuration can oscillate or produce a noisy "chatter" output if the applied differential input voltage is near the comparator's offset voltage. This usually occurs when the input signal is moving very slowly across the switching threshold of the comparator.

This problem can be prevented by the addition of hysteresis or positive feedback.

The hysteresis transfer curve is shown in Hysteresis Transfer Curve. This curve is a function of three components: V_{TH}, V_{OS}, and V_{HYST}:

- V_{TH} is the actual set voltage or threshold trip voltage.
- V_{OS} is the internal offset voltage between V_{IN+} and V_{IN-}. This voltage is added to V_{TH} to form the actual trip point at which the comparator must respond to change output states.
- V_{HYST} is the hysteresis (or trip window) that is designed to reduce comparator sensitivity to noise.

$V_{TH} + V_{OS} - (V_{HYST} / 2)$ $V_{TH} + V_{OS}$ $V_{TH} + V_{OS} + (V_{HYST} / 2)$
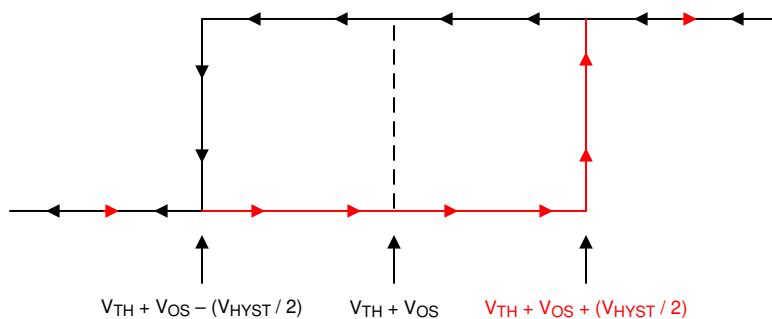
図 8-2. Hysteresis Transfer Curve

For more information, please see Application Note SBOA219 "Comparator with and without hysteresis circuit".

8.1.2.1 Inverting Comparator With Hysteresis

The inverting comparator with hysteresis requires a three-resistor network that is referenced to the comparator supply voltage (V+), as shown in 図 8-3.
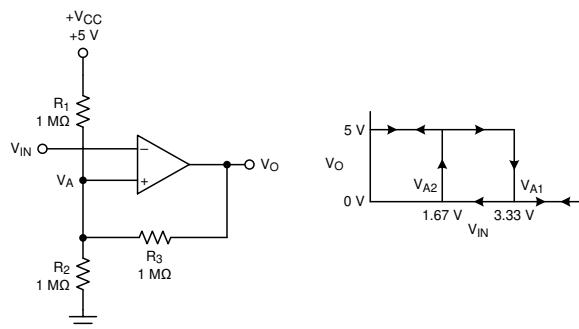

図 8-3. TLV4H390-SEP in an Inverting Configuration With Hysteresis

The equivalent resistor networks when the output is high and low are shown in 図 8-3.

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0
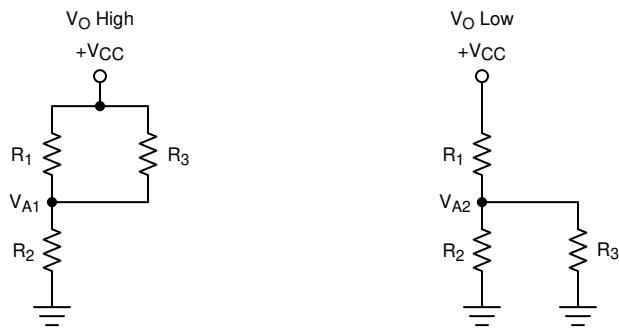
図 8-4. Inverting Configuration Resistor Equivalent Networks

When V_{IN} is less than V_A, the output voltage is high (for simplicity, assume V_O switches as high as V_{CC}). The three network resistors can be represented as R1 || R3 in series with R2, as shown in 図 8-4.

式 1 below defines the high-to-low trip voltage (V_{A1}).

$$V_{A1} = V_{CC} \times \frac{R2}{(R1 \parallel R3) + R2}$$

(1)

When V_{IN} is greater than V_A, the output voltage is low. In this case, the three network resistors can be presented as R2 || R3 in series with R1, as shown in 式 2.

Use 式 2 to define the low to high trip voltage (V_{A2}).

$$V_{A2} = V_{CC} \times \frac{R2 \parallel R3}{R1 + (R2 \parallel R3)}$$

(2)

式 3 defines the total hysteresis provided by the network.

$$\Delta V_A = V_{A1} - V_{A2}$$

(3)

8.1.2.2 Non-Inverting Comparator With Hysteresis

A noninverting comparator with hysteresis requires a two-resistor network and a voltage reference (V_{REF}) at the inverting input, as shown in TLV4H390-SEP in a Non-Inverting Configuration With Hysteresis,
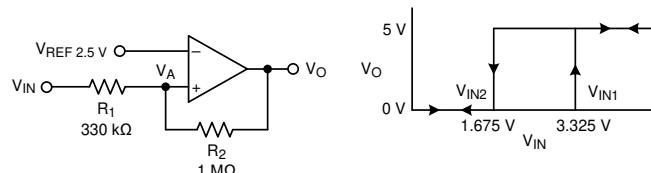

図 8-5. TLV4H390-SEP in a Non-Inverting Configuration With Hysteresis

The equivalent resistor networks when the output is high and low are shown in Non-Inverting Configuration Resistor Networks.

English Data Sheet: SNOSDF0
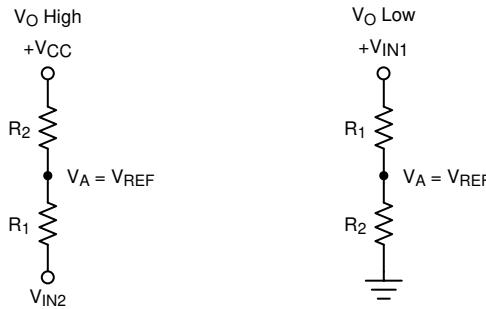
図 8-6. **Non-Inverting Configuration Resistor Networks**

When V_{IN} is less than V_{REF}, the output is low. For the output to switch from low to high, V_{IN} must rise above the V_{IN1} threshold. Use 式 4 to calculate V_{IN1}.

$$V_{IN1} = R1 \times \frac{V_{REF}}{R2} + V_{REF} \tag{4}$$

When V_{IN} is greater than V_{REF}, the output is high. For the comparator to switch back to a low state, V_{IN} must drop below V_{IN2}. Use 式 5 to calculate V_{IN2}.

$$V_{IN2} = \frac{V_{REF}\,(R1 + R2) - V_{CC} \times R1}{R2} \tag{5}$$

The hysteresis of this circuit is the difference between V_{IN1} and V_{IN2}, as shown in 式 6.

$$\Delta V_{IN} = V_{CC} \times \frac{R1}{R2} \tag{6}$$

For more information, please see Application Notes SNOA997 "Inverting comparator with hysteresis circuit" and SBOA313 "Non-Inverting Comparator With Hysteresis Circuit".

8.1.2.3 Inverting and Non-Inverting Hysteresis using Open-Drain Output

An open drain output device, such as the TLV4H390-SEP, can also be used, but the output pull-up resistor must also be taken into account in the calculations. The pull-up resistor is seen in series with the feedback resistor when the output is high. Thus, the feedback resistor is actually seen as R2 + R_{PULLUP}. TI recommends that the pull-up resistor be at least 10 times less than the feedback resistor value.

8.2 Typical Applications

8.2.1 Window Comparator

Window comparators are commonly used to detect undervoltage and overvoltage conditions. 図 8-7 shows a simple window comparator circuit. Window comparators require open drain outputs (TLV4H290-SEP) if the outputs are directly connected together.
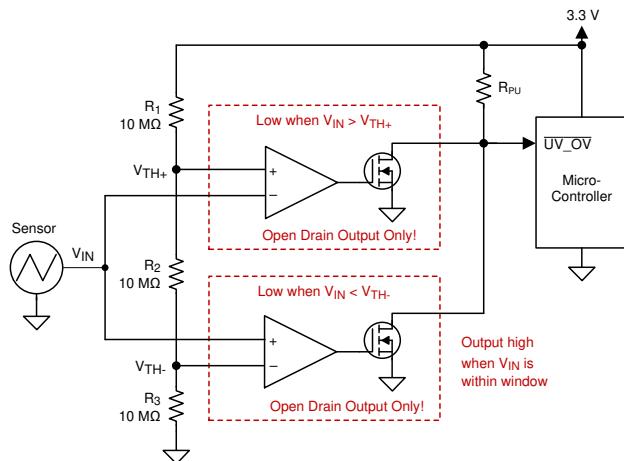
図 8-7. Window Comparator

8.2.1.1 Design Requirements

For this design, follow these design requirements:

- Alert (logic low output) when an input signal is less than 1.1V
- Alert (logic low output) when an input signal is greater than 2.2V
- Alert signal is active low
- Operate from a 3.3V power supply

8.2.1.2 Detailed Design Procedure

Configure the circuit as shown in 図 8-7. Connect V_{CC} to a 3.3V power supply and V_{EE} to ground. Make R1, R2 and R3 each 10MΩ resistors. These three resistors are used to create the positive and negative thresholds for the window comparator (V_{TH+} and V_{TH-}).

With each resistor being equal, V_{TH+} is 2.2V and V_{TH-} is 1.1V. Large resistor values such as 10MΩ are used to minimize power consumption. The resistor values can be recalculated to provide the desired trip point values.

The sensor output voltage is applied to the inverting and noninverting inputs of the two comparators. Using two open-drain output comparators allows the two comparator outputs to be Wire-OR'ed together.

The respective comparator outputs are low when the sensor is less than 1.1V or greater than 2.2V. The respective comparator outputs are high when the sensor is in the range of 1.1V to 2.2V (within the "window"), as shown in 図 8-8.

8.2.1.3 Application Curve
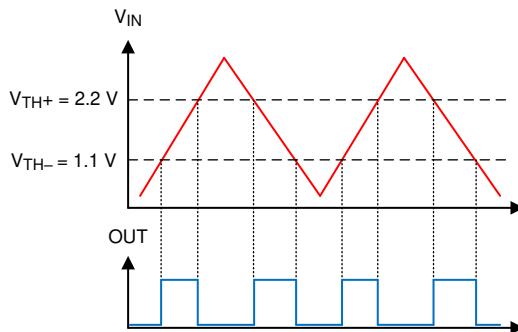
図 8-8. Window Comparator Results

For more information, please see Application note SBOA221 "Window comparator circuit".

8.2.2 Square-Wave Oscillator

Square-wave oscillator can be used as low cost timing reference or system supervisory clock source. A push-pull output (TLV4H390-SEP) is recommended for best symmetry.
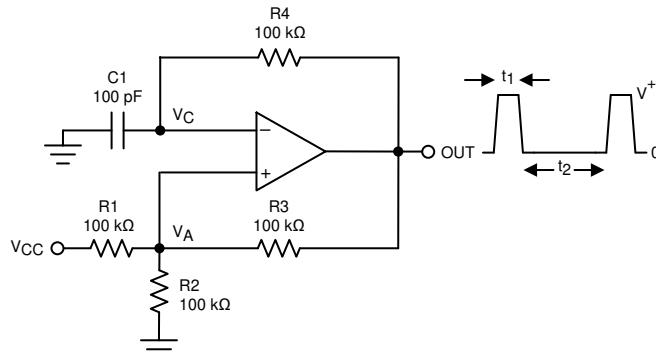

図 8-9. Square-Wave Oscillator

8.2.2.1 Design Requirements

The square-wave period is determined by the RC time constant of the capacitor C_1 and resistor R_4. The maximum frequency is limited by propagation delay of the device and the capacitance load at the output. The low input bias current allows a lower capacitor value and larger resistor value combination for a given oscillator frequency, which can help to reduce BOM cost and board space. R4 must be over several kilo-ohms to minimize loading the output.

8.2.2.2 Detailed Design Procedure

The oscillation frequency is determined by the resistor and capacitor values. The following calculation provides details of the steps.
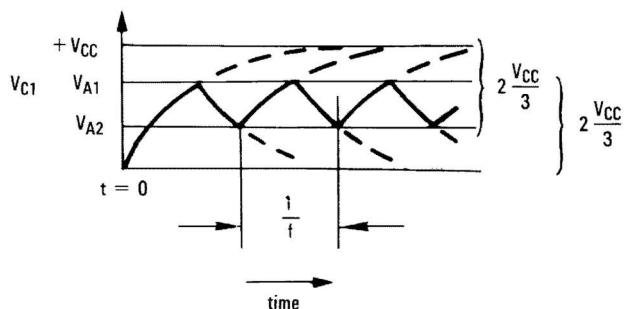

図 8-10. Square-Wave Oscillator Timing Thresholds

First consider the output of Figure 図 8-9 as high, which indicates the inverted input V_C is lower than the noninverting input (V_A). This causes the C_1 to be charged through R_4, and the voltage V_C increases until the inverting input is equal to the noninverting input. The value of V_A at the point is calculated by 式 7.

$$V_{A1} = \frac{V_{CC} \times R_2}{R_2 + R_1 \| R_3}$$

(7)

if $R_1 = R_2 = R_3$, then $V_{A1} = 2V_{CC} / 3$

At this time the comparator output trips pulling down the output to the negative rail. The value of V_A at this point is calculated by 式 8.

$$V_{A2} = \frac{V_{CC}(R_2 \| R_3)}{R_1 + R_2 \| R_3}$$

(8)

if $R_1 = R_2 = R_3$, then $V_{A2} = V_{CC}/3$

The C_1 now discharges though the R_4, and the voltage V_{CC} decreases until the input reaches V_{A2}. At this point, the output switches back to the starting state. The oscillation period equals to the time duration from for C_1 from $2V_{CC}/3$ to $V_{CC} / 3$ then back to $2V_{CC}/3$, which is given by $R_4 C_1 \times \ln 2$ for each trip. Therefore, the total time duration is calculated as $2 R_4 C_1 \times \ln 2$.

The oscillation frequency can be obtained by 式 9:

$$f = 1/(2\ R4 \times C1 \times \ln 2)$$

(9)

8.2.2.3 Application Curve

図 8-11 shows the simulated results of an oscillator using the following component values:

- $R_1 = R_2 = R_3 = R_4 = 100k\Omega$
- $C_1 = 100pF$, $C_L = 20pF$
- $V+ = 5V$, $V- = GND$
- C_{stray} (not shown) from V_A TO GND = 10pF
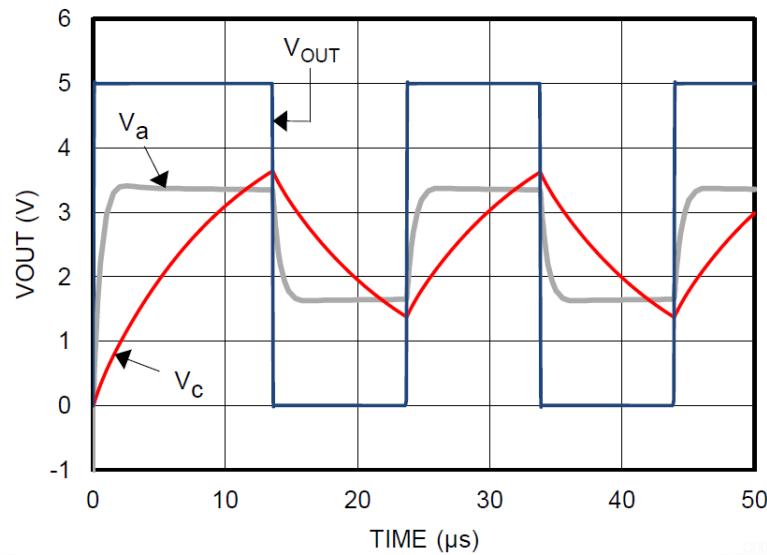
図 8-11. Square-Wave Oscillator Output Waveform

8.2.3 Adjustable Pulse Width Generator

The *Adjustable Pulse Width Generator* is a variation on the Square-Wave Oscillator that allows adjusting the pulse widths.

R_4 and R_5 provide separate charge and discharge paths for the capacitor C depending on the output state.
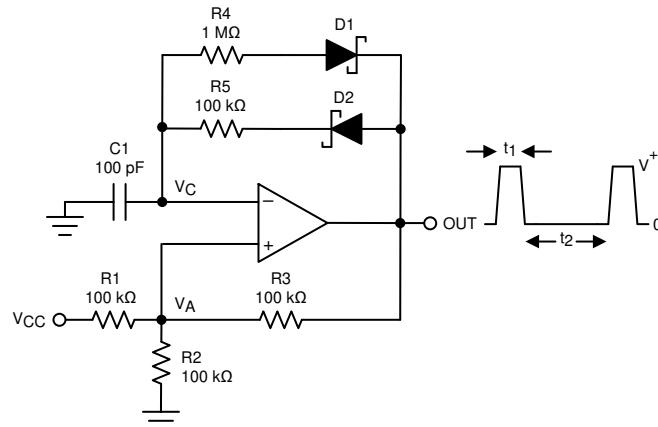
図 8-12. Adjustable Pulse Width Generator

The charge path is set through R_5 and D_2 when the output is high. Similarly, the discharge path for the capacitor is set by R_4 and D_1 when the output is low.

The pulse width t_1 is determined by the RC time constant of R_5 and C. Thus, the time t_2 between the pulses can be changed by varying R_4, and the pulse width can be altered by R_5. The frequency of the output can be changed by varying both R_4 and R_5. At low voltages, the effects of the diode forward drop (0.8V, or 0.15V for Shottky) must be taken into account by altering output high and low voltages in the calculations.

8.2.4 Time Delay Generator

The circuit shown in 図 8-13 provides output signals at a prescribed time interval from a time reference and automatically resets the output low when the input returns to 0V. This is useful for sequencing a "power on" signal to trigger a controlled start-up of power supplies.

図 8-13. Time Delay Generator

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0
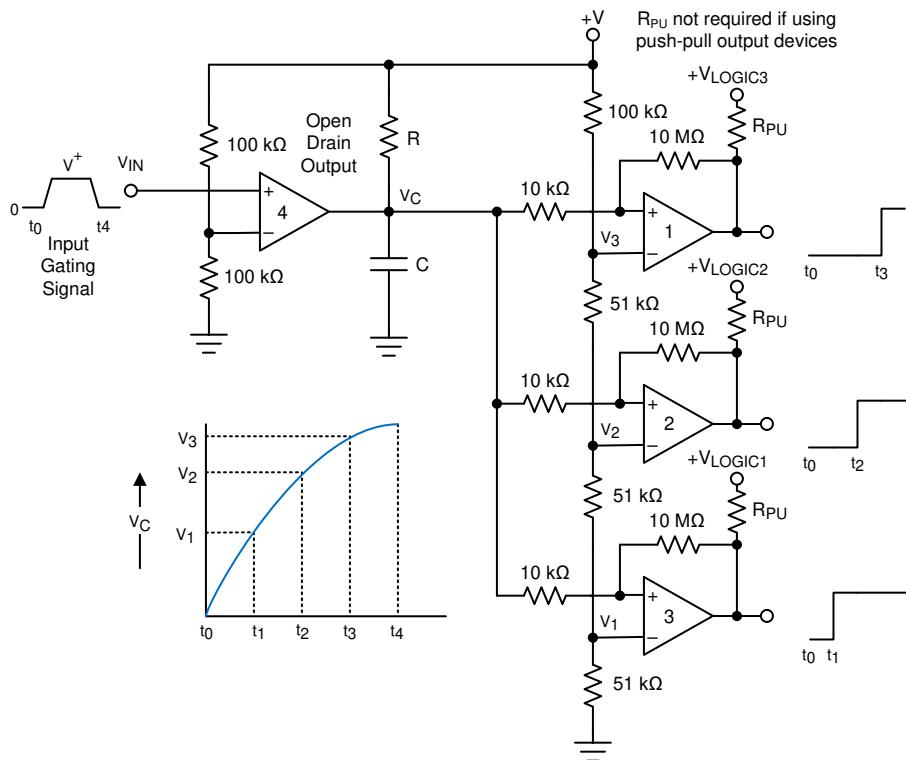
Consider the case of V_{IN} = 0. The output of comparator 4 is also at ground, "shorting" the capacitor and holding at 0V. This implies that the outputs of comparators 1, 2, and 3 are also at 0V. When an input signal is applied, the output of open drain comparator 4 goes High-Z and C charges exponentially through R. This is indicated in the graph. The output voltages of comparators 1, 2, and 3 switch to the high state in sequence when V_C rises above the reference voltages V_1, V_2 and V_3. A small amount of hysteresis has been provided by the 10kΩ and 10MΩ resistors to insure fast switching when the RC time constant is chosen to give long delay times. A good starting point is R = 100kΩ and C = 0.01µF to 1µF.

All outputs immediately go low when V_{IN} falls to 0V, due to the comparator output going low and immediately discharging the capacitor.

Comparator 4 must be a open-drain type output (TLV4H290-SEP), whereas comparators 1 though 3 can be either open drain or push-pull output, depending on system requirements. R_{PU} is not required for push-pull output devices.

8.2.5 Logic Level Shifter

The output of the TLV4H290-SEP is the uncommitted drain of the output transistor. Many open-drain outputs can be tied together to provide an output OR'ing function if desired.
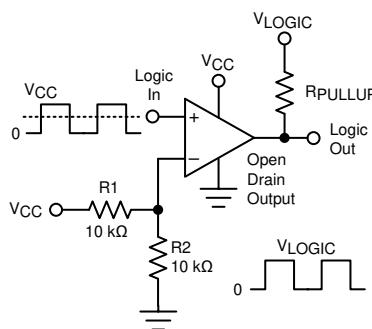

図 8-14. Universal Logic Level Shifter

The two 10kΩ resistors bias the input to half of the input logic supply level to set the threshold in the mid-point of the input logic levels. Only one shared output pull-up resistor is needed and can be connected to any pull-up voltage between 0V and 5.5V. The pullup voltage must match the driven logic input "high" level.

8.2.6 One-Shot Multivibrator
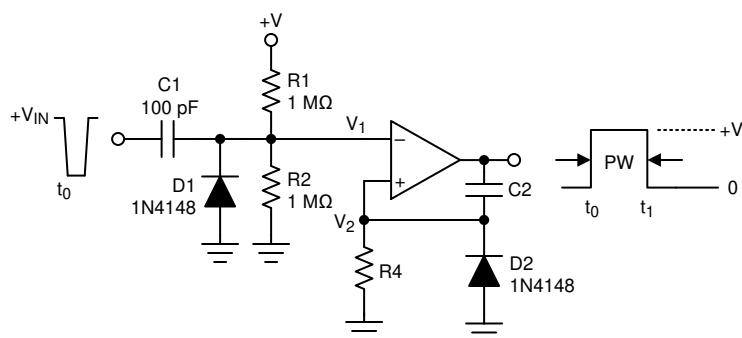
図 8-15. One-Shot Multivibrator

A monostable multivibrator has one stable state in which the output can remain indefinitely. The circuit can be triggered externally to another quasi-stable state. A monostable multivibrator can thus be used to generate a pulse of desired width.

The desired pulse width is set by adjusting the values of C_2 and R_4. The resistor divider of R_1 and R_2 can be used to determine the magnitude of the input trigger pulse. The output chnages state when $V_1 < V_2$. Diode D_2

provides a rapid discharge path for capacitor C_2 to reset at the end of the pulse. The diode also prevents the non-inverting input from being driven below ground.

### 8.2.7 Bi-Stable Multivibrator
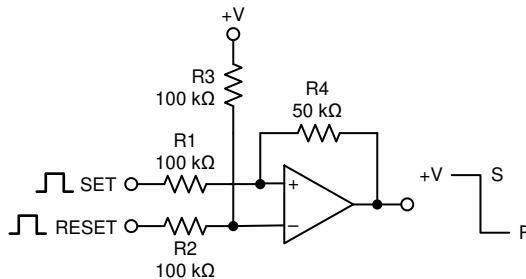
図 8-16. Bi-Stable Multivibrator

A bi-stable multivibrator has two stable states. The reference voltage is set up by the voltage divider of R_2 and R_3. A pulse applied to the SET terminal sets the output of the comparator high. The resistor divider of R_1, R_4, and R_5 now clamps the non-inverting input to a voltage greater than the reference voltage. A pulse applied to RESET toggles the output low.

8.2.8 Zero Crossing Detector
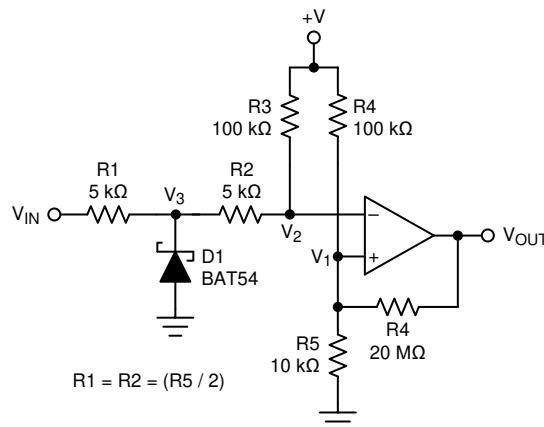
図 8-17. Zero Crossing Detector

A voltage divider of R_4 and R_5 establishes a reference voltage V_1 at the non-inverting input. By making the series resistance of R_1 and R_2 equal to R_5, the comparator switches when $V_{IN} = 0$. Diode D_1 imakes sure that V_3 clamps near ground. The voltage divider of R_2 and R_3 then prevents V_2 from going below ground. A small amount of hysteresis is setup to ensure rapid output voltage transitions.

8.2.9 Pulse Slicer

A Pulse Slicer is a variation of the Zero Crossing Detector and is used to detect the zero crossings on an input signal with a varying baseline level. This circuit works best with symmetrical waveforms. The RC network of R_1 and C_1 establishes an mean reference voltage V_{REF}, which tracks the mean amplitude of the V_{IN} signal. The noninverting input is directly connected to V_{REF} through R2. R2 and R3 are used to produce hysteresis to keep transitions free of spurious toggles. The time constant is a tradeoff between long-term symmetry and response time to changes in amplitude.

If the waveform is data, TI recommends that the data be encoded in NRZ (Non-Return to Zero) format to maintain proper average baseline. Asymmetrical inputs can suffer from timing distortions caused by the changing V_{REF} average voltage.

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: SNOSDF0
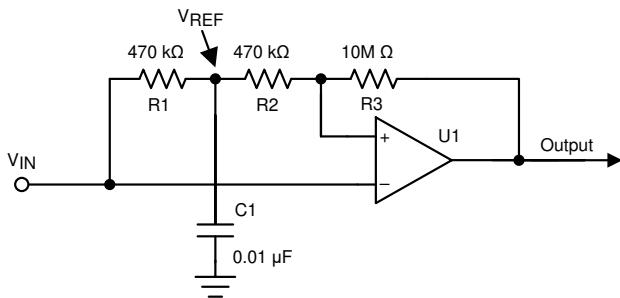
図 8-18. Pulse Slicer using TLV4H390-SEP

For this design, follow these design requirements:
- The RC constant value (R_2 and C_1) must support the targeted data rate to maintain a valid tripping threshold.
- The hysteresis introduced with R_2 and R_{43} helps to avoid spurious output toggles.

The TLV4H290-SEP may also be used, but with the addition of a pull-up resistor on the output (not shown for clarity).

図 8-19 shows the results of a 9600 baud data signal riding on a varying baseline.
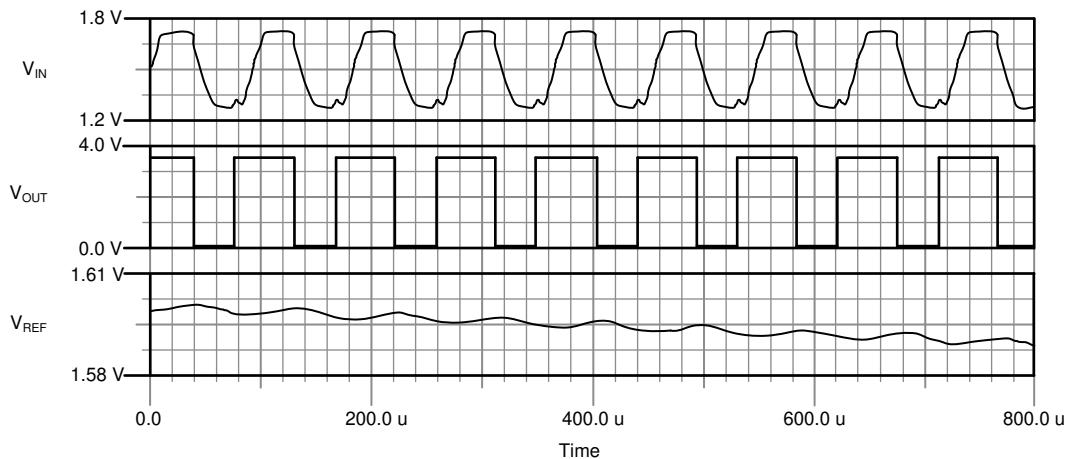

図 8-19. Pulse Slicer Waveforms

8.3 Power Supply Recommendations

Due to the fast output edges, bypass capacitors are critical to have on the supply pin to prevent supply ringing and false triggers and oscillations. Bypass the supply directly at *each* device with a low ESR 0.1μF ceramic bypass capacitor directly between V_{CC} pin and ground pins. Narrow, peak currents are drawn during the output transition time, particularly for the push-pull output device. These narrow pulses can cause un-bypassed supply lines and poor grounds to ring, possibly causing variation that can eat into the input voltage range and create an inaccurate comparison or even oscillations.

The device can be powered from either "split" supplies (V+, V- & GND), or a "single" supply (V+ and GND), with GND applied to the V- pin.

Input signals must stay within the specified input range (between V+ and V-) for either type.

Note that on "split" supplies, the output now swings "low" (V_{OL}) to V- potential and not GND.

8.4 Layout

8.4.1 Layout Guidelines

For accurate comparator applications, a stable power supply with minimized noise and glitches is required. Output rise and fall times are in the tens of nanoseconds, and must be treated as high speed logic devices. The bypass capacitor must be as close to the supply pin as possible and connected to a solid ground plane, and preferably directly between the V_{CC} and GND pins.

Minimize coupling between outputs and inputs to prevent output oscillations. Do not run output and input traces in parallel unless there is a V_{CC} or GND trace between output to reduce coupling. When series resistance is added to inputs, place the resistor close to the device. A low value (<100 ohms) resistor can also be added in series with the output to dampen any ringing or reflections on long, non-impedance controlled traces. For best edge shapes, controlled impedance traces with back-terminations must be used when routing long distances.

8.4.2 Layout Example

図 8-20. Layout Example

Copyright © 2025 Texas Instruments Incorporated

Product Folder Links: *TLV4H290-SEP TLV4H390-SEP*

English Data Sheet: *SNOSDF0*
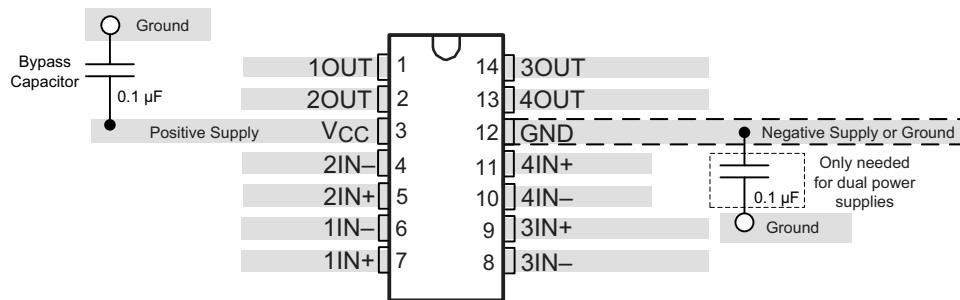
9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

Analog Engineers Circuit Cookbook: Amplifiers (See Comparators section) - SLYY137

Precision Design, Comparator with Hysteresis Reference Design— TIDU020

Window comparator circuit - SBOA221

Reference Design, Window Comparator Reference Design— TIPD178

Comparator with and without hysteresis circuit - SBOA219

Inverting comparator with hysteresis circuit - SNOA997

Non-Inverting Comparator With Hysteresis Circuit - SBOA313

Zero crossing detection using comparator circuit - SNOA999

PWM generator circuit - SBOA212

How to Implement Comparators for Improving Performance of Rotary Encoder in Industrial Drive Applications - SNOAA41

A Quad of Independently Func Comparators - SNOA654

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。 既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

リンクされているコンテンツは、各寄稿者により「現状のまま」提供されるものです。これらはテキサス・インスツルメンツの仕様を構成するものではなく、必ずしもテキサス・インスツルメンツの見解を反映したものではありません。テキサス・インスツルメンツの使用条件を参照してください。

9.4 Trademarks

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

9.5 静電気放電に関する注意事項

この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集　　　　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (May 2024) to Revision A (December 2024)   **Page**

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
P4H390MDYYTSEP	Active	Preproduction	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	-	Call TI	Call TI	-55 to 125	
P4H390MDYYTSEP.A	Active	Preproduction	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	-	Call TI	Call TI	-55 to 125	
TLV4H290MDYYTSEP	Active	Production	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	(4H290SEP, T4H290S EP)
TLV4H290MDYYTSEP.A	Active	Production	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	(4H290SEP, T4H290S EP)
TLV4H390MDYYTSEP	Active	Production	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	(4H390SEP, T4H390S EP)
V62/24636-01XE	Active	Production	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	(4H290SEP, T4H290S EP)
V62/24636-02XE	Active	Production	SOT-23-THIN (DYY) | 14	250 | SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	(4H390SEP, T4H390S EP)

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

PLASTIC SMALL OUTLINE

SEATING PLANE

PIN 1 INDEX AREA

C

⌐ 0.1 C

3.36 / 3.16

12X 0.5

A

1

14

4.3 / 4.1 NOTE 3

2X 3

7

8

4X 0° - 15°

1.1 MAX

B

2.1 / 1.9

14X 0.3 / 0.11

⊕ 0.1 Ⓜ C A B

4X 4° - 15°

0.2 / 0.08 TYP

SEE DETAIL A

0.25 GAUGE PLANE

0°- 8°

0.63 / 0.33

0.1 / 0.0

DETAIL A
TYP

4224643/D 07/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB

SYMM

14X (1.05)

1

14

14X (0.3)

SYMM

12X (0.5)

7

8

(R0.05) TYP

(3)
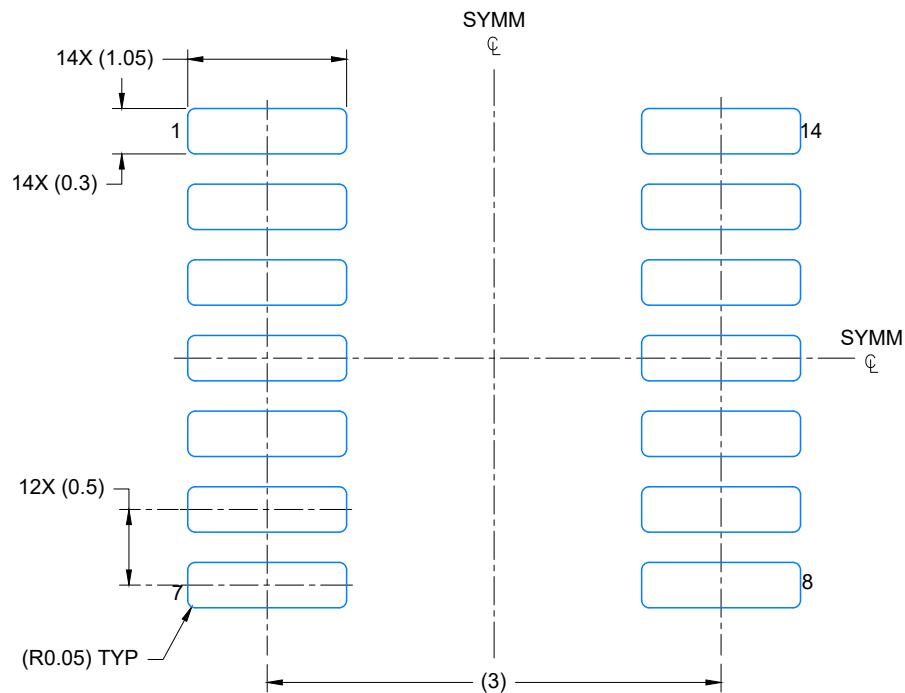
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

SOLDER MASK
OPENING

METAL

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

NON- SOLDER MASK
DEFINED
(PREFERRED)

SOLDER MASK
DEFINED
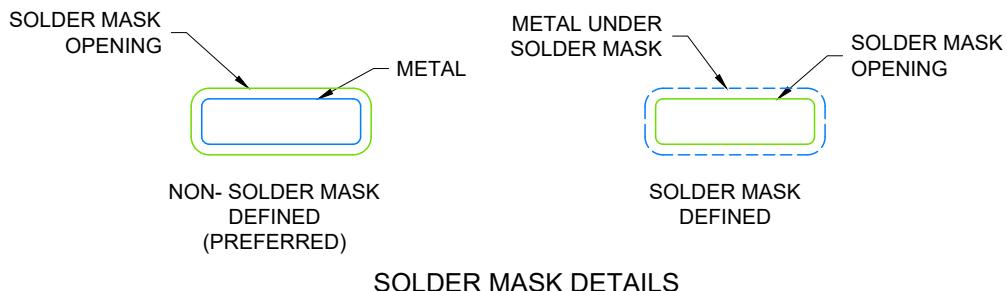
SOLDER MASK DETAILS

4224643/D   07/2024

NOTES: (continued)

6.   Publication IPC-7351 may have alternate designs.
7.   Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SYMM

14X (1.05)

14X (0.3)

12X (0.5)

(R0.05) TYP

1

14

7

8

(3)

SYMM
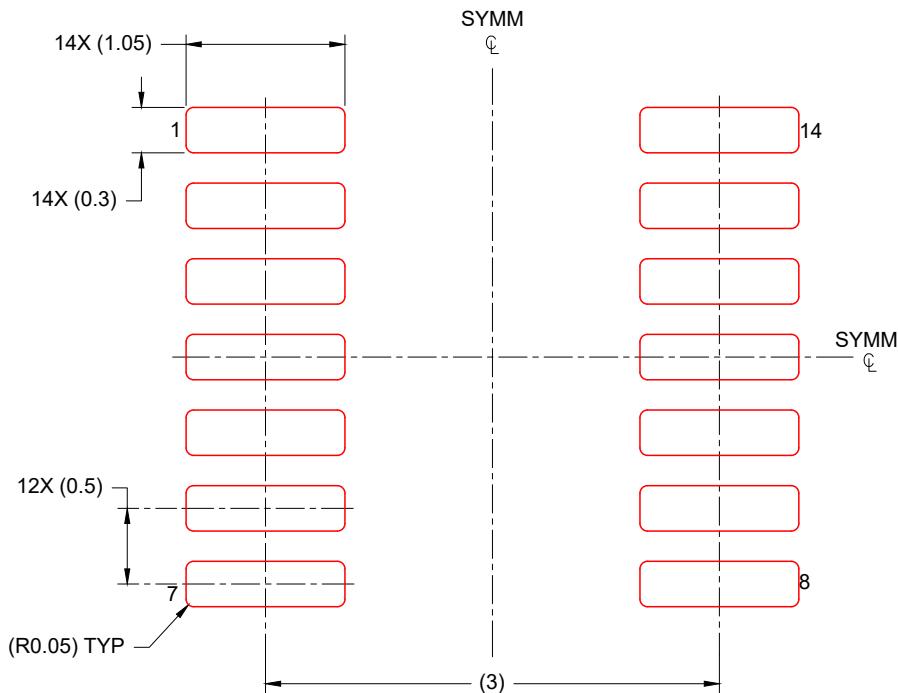
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

4224643/D   07/2024

NOTES: (continued)

8.   Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9.   Board assembly site may have different recommendations for stencil design.